74HC366-Q100; 74HCT366-Q100

Hex buffer/line driver; 3-state; inverting Rev. 3 — 13 March 2024

Product data sheet

1. General description

The 74HC366-Q100; 74HCT366-Q100 is a hex inverting buffer/line driver with 3-state outputs controlled by the output enable inputs ($\overline{\text{OEn}}$). A HIGH on $\overline{\text{OEn}}$ causes the outputs to assume a high impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 2.0 V to 6.0 V
- · CMOS low power dissipation
- · High noise immunity
- Latch-up performance exceeds 100 mA per JESD 78 Class II Level B
- Complies with JEDEC standards:
 - JESD8C (2.7 V to 3.6 V)
 - JESD7A (2.0 V to 6.0 V)
- Inverting outputs
- Input levels:
 - For 74HC366-Q100: CMOS level
 - For 74HCT366-Q100: TTL level
- ESD protection:
 - HBM: ANSI/ESDA/JEDEC JS-001 class 2 exceeds 2000 V
 - CDM: ANSI/ESDA/JEDEC JS-002 class C3 exceeds 1000 V

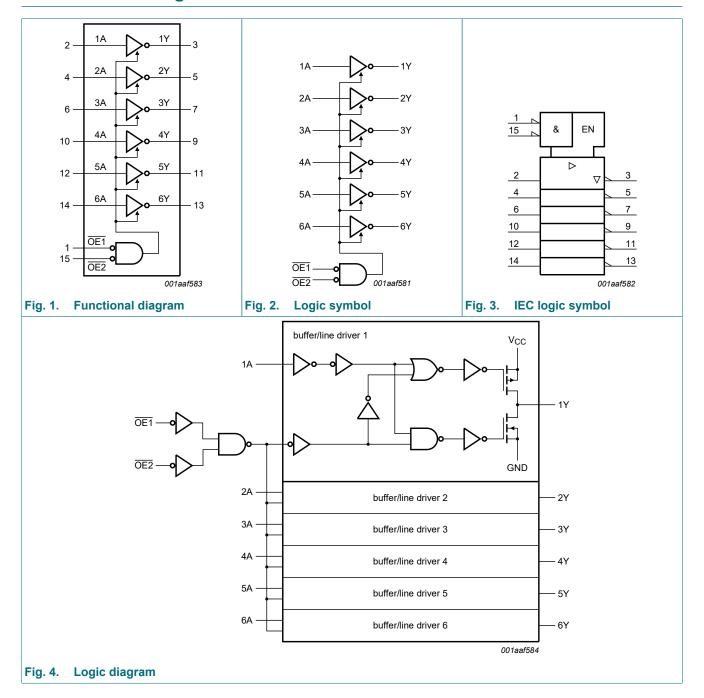
3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74HC366D-Q100	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads;	SOT109-1				
74HCT366D-Q100			body width 3.9 mm					
74HC366PW-Q100	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package;	SOT403-1				
74HCT366PW-Q100			16 leads; body width 4.4 mm					

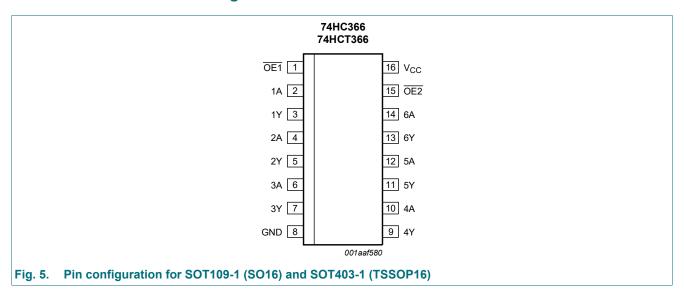


4. Functional diagram



5. Pinning information

5.1. Pinning



5.2. Pin description

Table 2. Pin description

Symbol	Pin	Description						
OE1, OE2	1, 15	output enable input (active LOW)						
1A, 2A, 3A, 4A, 5A, 6A	2, 4, 6, 10, 12, 14	data input						
1Y, 2Y, 3Y, 4Y, 5Y, 6Y	3, 5, 7, 9, 11, 13	data output						
GND	8	ground (0 V)						
V _{CC}	16	supply voltage						

6. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

		Input	Output
OE1	OE2	nA	nY
L	L	L	Н
L	L	Н	L
X	Н	Х	Z
Н	Х	Х	Z

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	V_{O} < -0.5 V or V_{O} > V_{CC} + 0.5 V	-	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-	±35	mA
I _{CC}	supply current		-	70	mA
I _{GND}	ground current		-	-70	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	[1]	-	500	mW

^[1] For SOT109-1 (SO16) package: P_{tot} derates linearly with 12.4 mW/K above 110 °C. For SOT403-1 (TSSOP16) package: P_{tot} derates linearly with 8.5 mW/K above 91 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC366-Q100		74HCT366-Q100			Unit	
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics 74HC366-Q100

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C		'			
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	V
		V _{CC} = 6.0 V	4.2	3.2	- - 0.5 1.35 1.8 - - - - - - - 0.1 0.1 0.26 0.26 ±0.1	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}	-	-	-	
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	0.5 1.35 1.8 - - - - - 0.1 0.1 0.1 0.26 5 0.26 ±0.1 ±0.5	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5		V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0		V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.98	4.32		V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.48	5.81	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	- 0.5 1.35 1.8 - - - - - - 0.1 0.1 0.26 0.26 ±0.1 ±0.5	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.5	μΑ
Icc	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	μΑ
Cı	input capacitance		-	3.5	-	pF

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -4	40 °C to +85 °C		I			
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.84	-	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.34	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.33	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-		V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$;	-	-	±1.0	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±5.0	μΑ
Icc	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	80	μΑ
T _{amb} = -4	40 °C to +125 °C		1			
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.7	-	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.2	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.4	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-	0.4	V
l _l	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±1.0	μA
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±10.0	1
I _{CC}	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 6.0$ V	_	_	160	μA

Table 7. Static characteristics 74HCT366-Q100

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	8.0	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
	voltage	I _O = -20 μA	4.4	4.5	-	V
		I _O = -6.0 mA	3.98	4.32	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
		I _O = 20 μA	-	0	0.1	V
		I _O = 6.0 mA	-	0.16	0.26	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.5	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	μΑ
ΔI _{CC}	additional supply current	$V_I = V_{CC}$ - 2.1 V; other inputs at V_{CC} or GND; $I_O = 0$ A				
		pins nA	-	100		μΑ
		pin OE1	-	100	360	μΑ
		pin OE2	-	90	320	μΑ
Cı	input capacitance		-	3.5	-	pF
T _{amb} = -4	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
		I _O = -20 μA	4.4	-	-	V
		I _O = -6.0 mA	3.84	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
		Ι _Ο = 20 μΑ	-	-	0.1	V
		I _O = 6.0 mA	-	-	0.33	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±1.0	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$			±5.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	80	μΑ
ΔI _{CC}	additional supply current	$V_I = V_{CC}$ - 2.1 V; other inputs at V_{CC} or GND; $I_O = 0$ A				
		pins nA	-	-	450	μΑ
		pin OE1	-	-	450	μΑ
		pin OE2	-	-	400	μΑ

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -4	0 °C to +125 °C		2.0			
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
		I _O = -20 μA	4.4	-	-	V
		I _O = -6.0 mA	3.7	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
		I _O = 20 μA	-	-	0.1	V
		I _O = 6.0 mA	-	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±1.0	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±10.0	μΑ
I _{CC}	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 5.5$ V	-	-	160	μΑ
ΔI _{CC}	additional supply current	$V_I = V_{CC} - 2.1 \text{ V}$; other inputs at V_{CC} or GND; $I_O = 0 \text{ A}$				
		pins nA	-	-	490	μΑ
		pin OE1	-	-	490	μΑ
		pin OE2	-	-	441	μΑ

10. Dynamic characteristics

Table 8. Dynamic characteristics 74HC366-Q100

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit Fig. 8.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
T _{amb} = 2	5 °C						
t _{pd}	propagation delay	nA to nY; see Fig. 6	[1]				
		V _{CC} = 2.0 V		-	33	100	ns
		V _{CC} = 4.5 V		-	12	20	ns
		V _{CC} = 5 V; C _L = 15 pF		-	10	-	ns
		V _{CC} = 6.0 V		-	10	100 20 - 17 150 30 26 150 30 26	ns
t _{en}	enable time	OEn to nY; see Fig. 7	[2]				
		V _{CC} = 2.0 V		-	44	150	ns
		V _{CC} = 4.5 V		-	16	100 20 - 17 150 30 26 150 30 26	ns
		V _{CC} = 6.0 V		-	13		ns
t _{dis}	disable time	OEn to nY; see Fig. 7	[3]				
		V _{CC} = 2.0 V		-	55	150	ns
		V _{CC} = 4.5 V		-	20	30	ns
		V _{CC} = 6.0 V		-	16	26	ns
t _t	transition time	see Fig. 6	[4]				
		V _{CC} = 2.0 V		-	14	60	ns
		V _{CC} = 4.5 V		-	5	12	ns
		V _{CC} = 6.0 V		-	4	10	ns
C _{PD}	power dissipation capacitance	per buffer; V_1 = GND to V_{CC}	[5]	-	30	-	pF

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
T _{amb} = -4	40 °C to +85 °C	,					
t _{pd}	propagation delay	nA to nY; see Fig. 6	[1]				
		V _{CC} = 2.0 V		-	-	125	ns
		V _{CC} = 4.5 V		-	-	25	ns
		V _{CC} = 6.0 V		-	-	21	ns
t _{en}	enable time	OEn to nY; see Fig. 7	[2]				
		V _{CC} = 2.0 V		-	-	190	ns
		V _{CC} = 4.5 V		-	-	38	ns
		V _{CC} = 6.0 V		-	-	33	ns
t _{dis}	disable time	OEn to nY; see Fig. 7	[3]				
		V _{CC} = 2.0 V		-	-	190	ns
		V _{CC} = 4.5 V		-	-	25 21 190 38 33	ns
		V _{CC} = 6.0 V		-	-	33	ns
t _t	transition time	see <u>Fig. 6</u>	[4]				
		V _{CC} = 2.0 V		-	-	125 25 21 190 38 33 190 38 33 75 15 13 26 225 45 38 225 45 38	ns
		V _{CC} = 4.5 V		-	-	15	ns
		V _{CC} = 6.0 V		-	-	13	ns
T _{amb} = -4	40 °C to +125 °C	'					
t _{pd}	propagation delay	nA to nY; see Fig. 6	[1]				
		V _{CC} = 2.0 V		-	-	150	ns
		V _{CC} = 4.5 V		-	-	30	ns
		V _{CC} = 6.0 V		-	-	25 21 190 38 33 190 38 33 75 15 13 26 225 45 38 225 45 38	ns
t _{en}	enable time	OEn to nY; see Fig. 7	[2]				
		V _{CC} = 2.0 V		-	-	225	ns
		V _{CC} = 4.5 V		-	-	45	ns
		V _{CC} = 6.0 V		-	-	38	ns
t _{dis}	disable time	OEn to nY; see Fig. 7	[3]				
		V _{CC} = 2.0 V		-	-	190 38 33 190 38 33 75 15 13 150 30 26 225 45 38 225 45 38	ns
		V _{CC} = 4.5 V		-	-	45	ns
		V _{CC} = 6.0 V		-	-	38	ns
t _t	transition time	see Fig. 6	[4]				
		V _{CC} = 2.0 V		-	-	90	ns
		V _{CC} = 4.5 V		-	-	18	ns
		V _{CC} = 6.0 V		-	-	15	ns

- t_{pd} is the same as t_{PHL} and t_{PLH} .
- \dot{t}_{en} is the same as t_{PZH} and t_{PZL} .
- t_{dis} is the same as t_{PHZ} and t_{PLZ} . [3]
- [4] t_t is the same as t_{THL} and t_{TLH}.
 [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs.}$

Table 9. Dynamic characteristics 74HCT366-Q100

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit Fig. 8.

Symbo	I Parameter	Conditions		Min	Тур	Max	Unit
T _{amb} = :	25 °C						
t _{pd}	propagation delay	nA to nY; see Fig. 6	[1]				
		V _{CC} = 4.5 V		-	13	24	ns
		V _{CC} = 5 V; C _L = 15 pF		-	11	-	ns
t _{en}	enable time	OEn to nY; V _{CC} = 4.5 V; see Fig. 7	[2]	-	16	35	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Fig. 7	[3]	-	20	35	ns
t _t	transition time	V _{CC} = 4.5 V; see <u>Fig. 6</u>	[4]	-	5	12	ns
C _{PD}	power dissipation capacitance	per buffer; V_I = GND to (V_{CC} - 1.5 V)	[5]	-	30	-	pF
T _{amb} =	-40 °C to +85 °C						
t _{pd}	propagation delay	nA to nY; V _{CC} = 4.5 V; see <u>Fig. 6</u>	[1]	-	-	30	ns
t _{en}	enable time	OEn to nY; V _{CC} = 4.5 V; see Fig. 7	[2]	-	-	44	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Fig. 7	[3]	-	-	44	ns
t _t	transition time	V _{CC} = 4.5 V; see <u>Fig. 6</u>	[4]	-	-	15	ns
T _{amb} =	-40 °C to +125 °C						•
t _{pd}	propagation delay	nA to nY; V _{CC} = 4.5 V; see <u>Fig. 6</u>	[1]	-	-	36	ns
t _{en}	enable time	OEn to nY; V _{CC} = 4.5 V; see Fig. 7	[2]	-	-	53	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Fig. 7	[3]	-	-	53	ns
t _t	transition time	V _{CC} = 4.5 V; see <u>Fig. 6</u>	[4]	-	-	18	ns

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- t_{en} is the same as t_{PZH} and t_{PZL}. [2]
- [3] t_{dis} is the same as t_{PHZ} and $t_{\text{PLZ}}.$
- t_{dls} is the same as t_{PHZ} and t_{PLZ}.
 t_t is the same as t_{THL} and t_{TLH}.
 C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 P_D = C_{PD} x V_{CC}² x f_i x N + Σ(C_L x V_{CC}² x f_o) where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

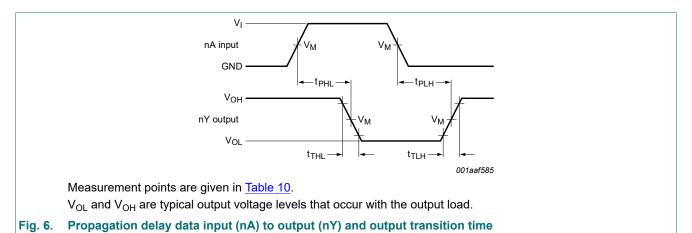
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs.}$

10.1. Waveforms and test circuit



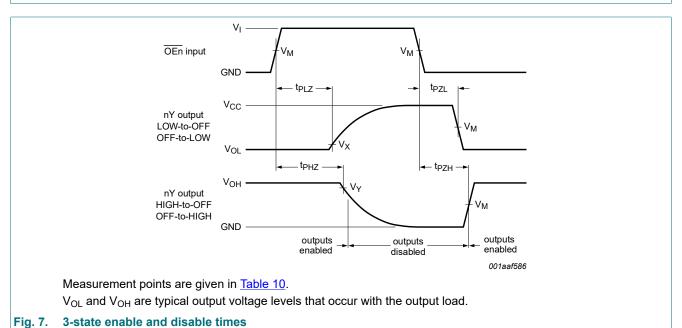
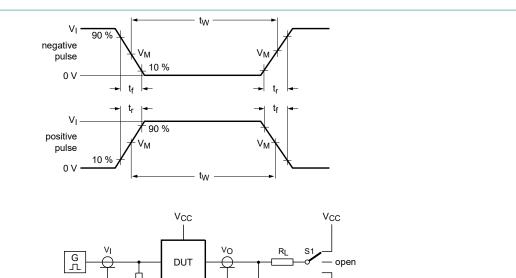


Table 10. Measurement points

Туре	Input	Output			
	V _M	V _M	V _X	V _Y	
74HC366-Q100	0.5V _{CC}	0.5V _{CC}	0.1 x V _{CC}	0.9 x V _{CC}	
74HCT366-Q100	1.3 V	1.3 V	0.1 x V _{CC}	0.9 x V _{CC}	



001aad983

Test data is given in Table 11.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistance

S1 = Test selection switch

Fig. 8. Test circuit for measuring switching times

Table 11. Test data

Туре	Input		Load		S1 position		
	V _I	t _r , t _f	CL	R_L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t_{PZL}, t_{PLZ}
74HC366-Q100	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}
74HCT366-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}

11. Package outline

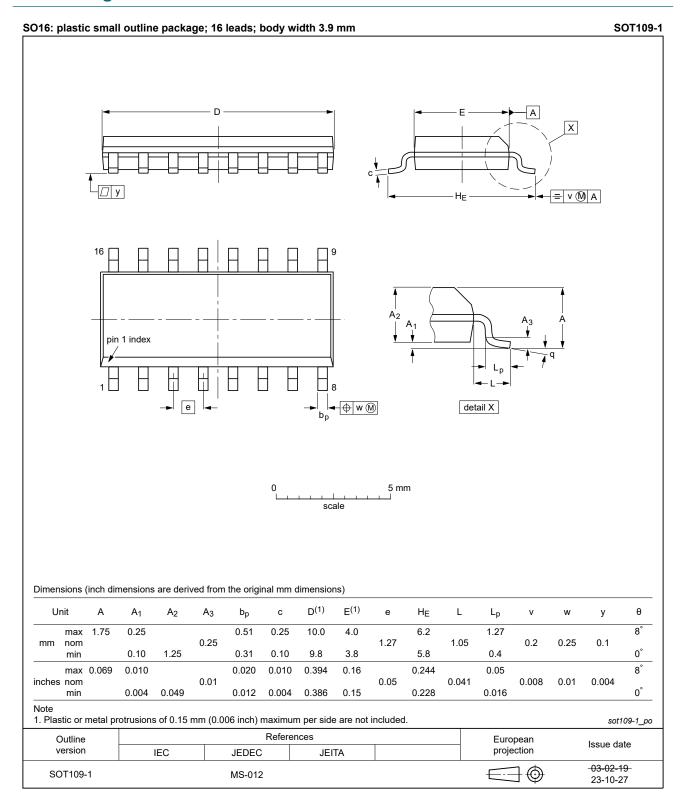


Fig. 9. Package outline SOT109-1 (SO16)

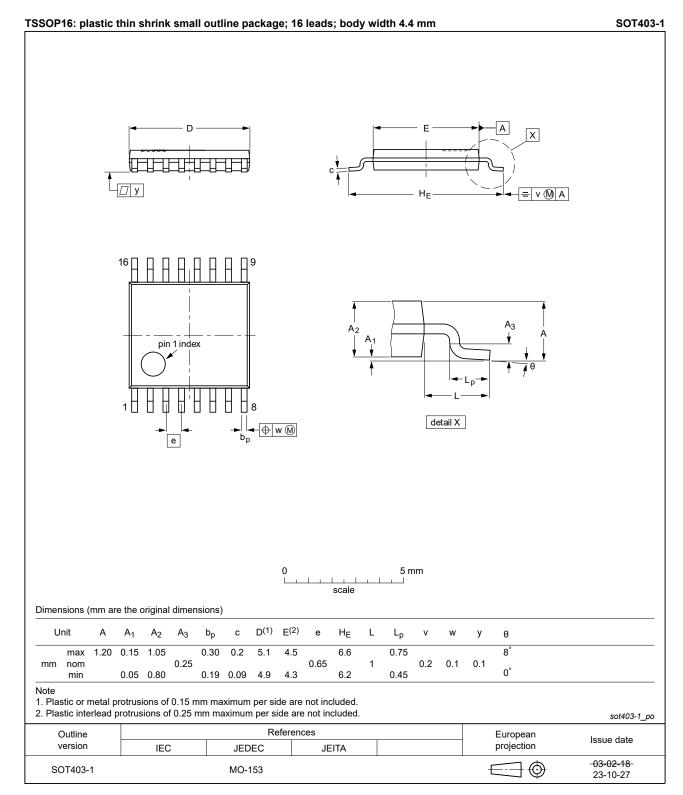


Fig. 10. Package outline SOT403-1 (TSSOP16)

12. Abbreviations

Table 12. Abbreviations

Table 12. Appleviations			
Acronym	Description		
CDM	Charged Device Model		

74HC_HCT366_Q100

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Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model

13. Revision history

Table 13. Revision history

Table 15. Nevision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
74HC_HCT366_Q100 v.3	20240313	Product data sheet	-	74HC_HCT366_Q100 v.2	
Modifications:		D specification updated accord 10: Aligned SO and TSSOP p	•		
74HC_HCT366_Q100 v.2	20210217	Product data sheet	-	74HC_HCT366_Q100 v.1	
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section 1 and Section 2 updated. Section 7: Derating values for P_{tot} total power dissipation updated. Table 7: Conditions for I_{OZ} have changed for 74HCT366-Q100. (errata) 				
74HC_HCT366_Q100 v.1	20120807	Product data sheet	-	-	

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Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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74HC_HCT366_Q100

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